Yasuhisa Sano

List of Publications by Year
in descending order

170	3,957	147801	138484
papers	citations	31 h-index	58 g-index

173	173	173	2001
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Hard x-ray intensity autocorrelation using direct two-photon absorption. Physical Review Research, 2022, 4, .	3.6	8
2	High-Speed Etching of Silicon Carbide Wafer Using High-Pressure SF₆ Plasma. ECS Journal of Solid State Science and Technology, 2021, 10, 014005.	1.8	5
3	Photoelectrochemical Oxidation Assisted Catalyst-Referred Etching for SiC (0001) Surface. International Journal of Automation Technology, 2021, 15, 74-79.	1.0	9
4	X-ray adaptive zoom condenser utilizing an intermediate virtual focus. Optics Express, 2021, 29, 15604.	3.4	2
5	(Invited) High-Speed Plasma Etching of SiC Wafer Toward Backside Thinning. ECS Transactions, 2021, 104, 85-92.	0.5	1
6	(Invited) High-Speed Plasma Etching of SiC Wafer Toward Backside Thinning. ECS Meeting Abstracts, 2021, MA2021-02, 992-992.	0.0	0
7	Optimal deformation procedure for hybrid adaptive x-ray mirror based on mechanical and piezo-driven bending system. Review of Scientific Instruments, 2021, 92, 123706.	1.3	3
8	High-throughput deterministic plasma etching using array-type plasma generator system. Review of Scientific Instruments, 2021, 92, 125107.	1.3	0
9	An abrasive-free chemical polishing method assisted by nickel catalyst generated by in situ electrochemical plating. Review of Scientific Instruments, 2020, 91, 045108.	1.3	6
10	Adaptive x-ray zoom condenser system based on concave and convex mirrors. , 2020, , .		1
11	High-resolution micro channel-cut crystal monochromator processed by plasma chemical vaporization machining for a reflection self-seeded X-ray free-electron laser. Optics Express, 2020, 28, 25706.	3.4	6
12	Improvements in graphene growth on 4H-SiC(0001) using plasma induced surface oxidation. Journal of Applied Physics, 2019, 126, 065301.	2.5	2
13	Catalyzed chemical polishing of SiO2 glasses in pure water. Review of Scientific Instruments, 2019, 90, 045115.	1.3	15
14	High-Efficiency Planarization of SiC Wafers by Water-CARE (Catalyst-Referred Etching) Employing Photoelectrochemical Oxidation. Materials Science Forum, 2019, 963, 525-529.	0.3	2
15	A micro channel-cut crystal X-ray monochromator for a self-seeded hard X-ray free-electron laser. Journal of Synchrotron Radiation, 2019, 26, 1496-1502.	2.4	9
16	X-ray optics for advanced ultrafast pumpâ€“probe X-ray experiments at SACLA. Journal of Synchrotron Radiation, 2019, 26, 333-338.	2.4	22
17	Compact reflective imaging optics in hard X-ray region based on concave and convex mirrors. Optics Express, 2019, 27, 3429.	3.4	12
18	Fabrication of Optics with a Thin Part by Plasma Chemical Vaporization Machining. , 2019, , .		0

#	Article	IF	Citations
19	Surface Finishing Method Using Plasma Chemical Vaporization Machining for Narrow Channel Walls of X-Ray Crystal Monochromators. International Journal of Automation Technology, 2019, 13, 246-253.	1.0	4
20	Figuring of fused silica optical surface with thin parts by plasma chemical vaporization machining. , 2019, , .		0
21	Platinum-catalyzed hydrolysis etching of SiC in water: A density functional theory study. Japanese Journal of Applied Physics, 2018, 57, 055703.	1.5	10
22	Polishing Technique of Next-Generation Power Semiconductor SiC Substrate. Journal of the Japan Society for Precision Engineering, 2018, 84, 217-220.	0.1	0
23	Nearly diffraction-limited hard X-ray line focusing with hybrid adaptive X-ray mirror based on mechanical and piezo-driven deformation. Optics Express, 2018, 26, 17477.	3.4	9
24	Performance of a hard X-ray split-and-delay optical system with a wavefront division. Journal of Synchrotron Radiation, 2018, 25, 20-25.	2.4	25
25	Characteristics and Mechanism of Catalyst-Referred Etching Method: Application to 4H-SiC. International Journal of Automation Technology, 2018, 12, 154-159.	1.0	8
26	The Polishing Effect of SiC Substrates in Femtosecond Laser Irradiation Assisted Chemical Mechanical Polishing (CMP). ECS Journal of Solid State Science and Technology, 2017, 6, P105-P112.	1.8	35
27	Simulation of concaveâ€“convex imaging mirror system for development of a compact and achromatic full-field x-ray microscope. Applied Optics, 2017, 56, 967.	2.1	14
28	Characterization of temporal coherence of hard X-ray free-electron laser pulses with single-shot interferograms. IUCrJ, 2017, 4, 728-733.	2.2	32
29	Development of concave-convex imaging mirror system for a compact and achromatic full-field x-ray microscope. , 2017, , .		0
30	Nearly diffraction-limited X-ray focusing with variable-numerical-aperture focusing optical system based on four deformable mirrors. Scientific Reports, 2016, 6, 24801.	3.3	41
31	Development of speckle-free channel-cut crystal optics using plasma chemical vaporization machining for coherent x-ray applications. Review of Scientific Instruments, 2016, 87, 063118.	1.3	14
32	Simulation and Experimental Study of Wavefront Measurement Accuracy of the Pencil-Beam Method. Synchrotron Radiation News, 2016, 29, 32-36.	0.8	7
33	Wavelength-tunable split-and-delay optical system for hard X-ray free-electron lasers. Optics Express, 2016, 24, 9187.	3.4	52
34	High-efficiency planarization method combining mechanical polishing and atmospheric-pressure plasma etching for hard-to-machine semiconductor substrates. Mechanical Engineering Journal, 2016, 3, 15-00527-15-00527.	0.4	0
35	Development of ion beam figuring system with electrostatic deflection for ultraprecise X-ray reflective optics. Review of Scientific Instruments, 2015, 86, 093103.	1.3	11
36	Catalystâ€Assisted Electroless Flattening of Ge Surfaces in Dissolvedâ€O₂â€Containing Water. ChemElectroChem, 2015, 2, 1656-1659.	3.4	5

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37	Damage threshold of platinum/carbon multilayers under hard X-ray free-electron laser irradiation. Optics Express, 2015, 23, 29032.	3.4	14
38	Hard X-ray nanofocusing using adaptive focusing optics based on piezoelectric deformable mirrors. Review of Scientific Instruments, 2015, 86, 043102.	1.3	21
39	Numerically controlled atmospheric-pressure plasma sacrificial oxidation using electrode arrays for improving silicon-on-insulator layer uniformity. Japanese Journal of Applied Physics, 2015, 54, 01AE03.	1.5	4
40	Local atomic configuration of graphene, buffer layer, and precursor layer on SiC(0001) by photoelectron diffraction. Surface Science, 2015, 632, 98-102.	1.9	7
41	Plasma-Based Nanomanufacturing Under Atmospheric Pressure. , 2015, , 1529-1547.		0
42	Atomically controlled surfacing of single crystalline SiC and GaN by catalyst-referred etching. , 2014, , .		0
43	Dicing of SiC Wafer by Atmospheric-Pressure Plasma Etching Process with Slit Mask for Plasma Confinement. Materials Science Forum, 2014, 778-780, 759-762.	0.3	2
44	Generation of 1020â€‰Wâ€‰cmâ^’2 hard X-ray laser pulses with two-stage reflective focusing system. Nature Communications, 2014, 5, 3539.	12.8	124
45	Aggregation of carbon atoms at SiO2/SiC(0 0 0 1) interface by plasma oxidation toward formation of pit-free graphene. Carbon, 2014, 80, 440-445.	10.3	5
46	Enhancement of photoluminescence efficiency from GaN(0001) by surface treatments. Japanese Journal of Applied Physics, 2014, 53, 021001.	1.5	9
47	Development of basic-type CMP/P-CVM fusion processing system (Type A) and its fundamental characteristics. , 2014, , .		2
48	Development of split-delay x-ray optics using Si(220) crystals at SACLA. Proceedings of SPIE, 2014, , .	0.8	10
49	Planarization of SiC and GaN Wafers Using Polishing Technique Utilizing Catalyst Surface Reaction. ECS Journal of Solid State Science and Technology, 2013, 2, N3028-N3035.	1.8	24
50	Focusing of X-ray free-electron laser pulses with reflective optics. Nature Photonics, 2013, 7, 43-47.	31.4	234
51	X-ray nanofocusing using a piezoelectric deformable mirror and at-wavelength metrology methods. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2013, 710, 93-97.	1.6	11
52	A Bragg beam splitter for hard x-ray free-electron lasers. Optics Express, 2013, 21, 2823.	3.4	55
53	Damage characteristics of platinum/carbon multilayers under x-ray free-electron laser irradiation. Proceedings of SPIE, 2013, , .	0.8	3
54	Plasma-Based Nanomanufacturing Under Atmospheric Pressure. , 2013, , 1-17.		2

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55	Surface Observation of 4H-SiC (0001) Planarized by Catalyst-Referred Etching. Key Engineering Materials, 2012, 516, 452-456.	0.4	0
56	High-Resolution TEM Observation of 4H-SiC (0001) Surface Planarized by Catalyst-Referred Etching. Materials Science Forum, 2012, 717-720, 873-876.	0.3	6
57	Rapid Planarization Method by Ultraviolet Light Irradiation for Gallium Nitride Using Platinum Catalyst. Key Engineering Materials, 2012, 523-524, 46-49.	0.4	2
58	Improvement of Removal Rate in Abrasive-Free Planarization of 4H-SiC Substrates Using Catalytic Platinum and Hydrofluoric Acid. Japanese Journal of Applied Physics, 2012, 51, 046501.	1.5	10
59	Hard-X-ray imaging optics based on four aspherical mirrors with 50 nm resolution. Optics Express, 2012, 20, 10310.	3.4	27
60	Shape correction of optical surfaces using plasma chemical vaporization machining with a hemispherical tip electrode. Applied Optics, 2012, 51, 401.	1.8	12
61	Experimental and simulation study of undesirable short-period deformation in piezoelectric deformable x-ray mirrors. Review of Scientific Instruments, 2012, 83, 053701.	1.3	12
62	Atomically Smooth Gallium Nitride Surfaces Prepared by Chemical Etching with Platinum Catalyst in Water. Journal of the Electrochemical Society, 2012, 159, H417-H420.	2.9	36
63	Improved reflectivity of platinum/carbon multilayers for X-ray mirrors by carbon doping into platinum layer. Current Applied Physics, 2012, 12, S20-S23.	2.4	8
64	Structural and chemical characteristics of atomically smooth GaN surfaces prepared by abrasive-free polishing with Pt catalyst. Journal of Crystal Growth, 2012, 349, 83-88.	1.5	32
65	Adsorption of hydrogen fluoride on SiC surfaces: A density functional theory study. Current Applied Physics, 2012, 12, S42-S46.	2.4	14
66	Atomically controlled chemical polishing of GaN using platinum and hydrofluoric acid. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 433-435.	0.8	4
67	Improvement of Removal Rate in Abrasive-Free Planarization of 4H-SiC Substrates Using Catalytic Platinum and Hydrofluoric Acid. Japanese Journal of Applied Physics, 2012, 51, 046501.	1.5	10
68	TEM Observation of 8 Deg Off-Axis 4H-SiC (0001) Surfaces Planarized by Catalyst-Referred Etching. Materials Science Forum, 2011, 679-680, 489-492.	0.3	6
69	Evaluation of Schottky Barrier Diodes Fabricated Directly on Processed 4H-SiC(0001) Surfaces. Journal of Nanoscience and Nanotechnology, 2011, 11, 2809-2813.	0.9	1
70	Dependence of Process Characteristics on Atomic-Step Density in Catalyst-Referred Etching of 4Hâ€“SiC(0001) Surface. Journal of Nanoscience and Nanotechnology, 2011, 11, 2928-2930.	0.9	30
71	Numerically controlled sacrificial plasma oxidation using array-type electrode toward high-throughput deterministic machining. International Journal of Nanomanufacturing, 2011, 7, 289.	0.3	0
72	Formation of wide and atomically flat graphene layers on ultraprecision-figured 4H-SiC(0001) surfaces. Surface Science, 2011, 605, 597-605.	1.9	26

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73	Single-nanometer focusing of hard x-rays by Kirkpatrickâ€“Baez mirrors. Journal of Physics Condensed Matter, 2011, 23, 394206.	1.8	117
74	Abrasive-Free Planarization of 3-Inch 4H-SiC Substrate Using Catalyst-Referred Etching. Materials Science Forum, 2011, 679-680, 493-495.	0.3	3
75	Mechanism of atomic-scale passivation and flattening of semiconductor surfaces by wet-chemical preparations. Journal of Physics Condensed Matter, 2011, 23, 394202.	1.8	6
76	Extended knife-edge method for characterizing sub-10-nm X-ray beams. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 616, 246-250.	1.6	8
77	Stitching-angle measurable microscopic-interferometer: Surface-figure metrology tool for hard X-ray nanofocusing mirrors with large curvature. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2010, 616, 203-206.	1.6	21
78	Breaking the 10â€‰nm barrier in hard-X-ray focusing. Nature Physics, 2010, 6, 122-125.	16.7	484
79	Development of nanometer level accurate computer-controlled figuring with high spatial resolution and its application to hard X-ray focusing mirror. Journal of the Japan Society for Precision Engineering, 2010, 76, 338-342.	0.1	1
80	Reduction of Surface Roughness of 4H-SiC by Catalyst-Referred Etching. Materials Science Forum, 2010, 645-648, 775-778.	0.3	16
81	Beveling of Silicon Carbide Wafer by Plasma Etching Using Atmospheric-Pressure Plasma. Japanese Journal of Applied Physics, 2010, 49, 08JJ03.	1.5	4
82	Removal characteristics of plasma chemical vaporization machining with a pipe electrode for optical fabrication. Applied Optics, 2010, 49, 4434.	2.1	16
83	Wavefield characterization of nearly diffraction-limited focused hard x-ray beam with size less than 10 nm. Review of Scientific Instruments, 2010, 81, 123704.	1.3	19
84	Termination dependence of surface stacking at<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi><mml:mtext>-SiC</mml:mtext><mml:mrow><mml:mo>(</m Density functional theory calculations. Physical Review B, 2009, 79, .	3.2	23
85	Wavefront Control System for Phase Compensation in Hard X-ray Optics. Japanese Journal of Applied Physics, 2009, 48, 072503.	1.5	32
86	Novel Scheme of Figure-Error Correction for X-ray Nanofocusing Mirror. Japanese Journal of Applied Physics, 2009, 48, 096507.	1.5	2
87	A Study on a Surface Preparation Method for Single-Crystal SiC Using an Fe Catalyst. Journal of Electronic Materials, 2009, 38, 159-163.	2.2	33
88	Stitching interferometric measurement system for hard x-ray nanofocusing mirrors. Journal of Physics: Conference Series, 2009, 186, 012080.	0.4	0
89	Catalystâ€referred etching of 4Hï¿¿SiC substrate utilizing hydroxyl radicals generated from hydrogen peroxide molecules. Surface and Interface Analysis, 2008, 40, 998-1001.	1.8	44
90	Stitching interferometric metrology for steeply curved xâ€ray mirrors. Surface and Interface Analysis, 2008, 40, 1023-1027.	1.8	13

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91	Etching characteristics of GaN by plasma chemical vaporization machining. Surface and Interface Analysis, 2008, 40, 1566-1570.	1.8	8
92	Ultraprecision finishing technique by numerically controlled sacrificial oxidation. Journal of Crystal Growth, 2008, 310, 2173-2177.	1.5	10
93	Defect-Free Planarization of 4Hâ€“SiC(0001) Substrate Using Reference Plate. Japanese Journal of Applied Physics, 2008, 47, 104-107.	1.5	15
94	Beveling of Silicon Carbide Wafer by Plasma Chemical Vaporization Machining. Materials Science Forum, 2008, 600-603, 843-846.	0.3	4
95	Direct determination of the wave field of an x-ray nanobeam. Physical Review A, 2008, 77, .	2.5	38
96	Hard X-ray Focusing less than 50nm for Nanoscopy/spectroscopy. AIP Conference Proceedings, 2007, , .	0.4	1
97	Fabrication of X-ray Mirror for Hard X-ray Diffraction Limited Nanofocusing. AIP Conference Proceedings, 2007, , .	0.4	0
98	Fabrication of ultrathin and highly uniform silicon on insulator by numerically controlled plasma chemical vaporization machining. Review of Scientific Instruments, 2007, 78, 086102.	1.3	20
99	Atomic-scale flattening of SiC surfaces by electroless chemical etching in HF solution with Pt catalyst. Applied Physics Letters, 2007, 90, 202106.	3.3	79
100	Polishing Characteristics of 4H-SiC Si-Face and C-Face by Plasma Chemical Vaporization Machining. Materials Science Forum, 2007, 556-557, 757-760.	0.3	0
101	Damage-Free Planarization of 4H-SiC (0001) by Catalyst-Referred Etching. Materials Science Forum, 2007, 556-557, 749-751.	0.3	15
102	Development of Ultra Precision Finishing Method for Quartz Crystal Wafer Utilizing Atmospheric Pressure Plasma. , 2007, , 233-237.		0
103	Atomic-scale Characterization of HF-treated 4H-SiC(0001)1Ã—1 Surfaces by Scanning Tunneling Microscopy. Materials Research Society Symposia Proceedings, 2007, 996, 1.	0.1	0
104	Hard x-ray wavefront measurement and control for hard x-ray nanofocusing. , 2007, , .		0
105	Novel Abrasive-free Planarization of Si and SiC using Catalyst. , 2007, , 267-270.		8
106	Efficient focusing of hard x rays to 25nm by a total reflection mirror. Applied Physics Letters, 2007, 90, 051903.	3.3	203
107	Catalyst-referred etching of silicon. Science and Technology of Advanced Materials, 2007, 8, 162-165.	6.1	8
108	Fabrication of damascene Cu wirings using solid acidic catalyst. Science and Technology of Advanced Materials, 2007, 8, 166-169.	6.1	2

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109	Investigation of the Surface Removal Process of Silicon Carbide in Elastic Emission Machining. Journal of Electronic Materials, 2007, 36, 92-97.	2.2	15
110	Surface gradient integrated profiler for X-ray and EUV optics. Science and Technology of Advanced Materials, 2007, 8, 177-180.	6.1	5
111	Ultraprecision Finishing of Photomask Substrate by Utilizing Atmospheric Pressure Plasma. , 2007, , 227-231.		0
112	Fabrication of Ultraprecisely Figured Mirror for Nano Focusing Hard-x-ray. , 2007, , 295-300.		0
113	Ultraprecision Finishing Process for Improving Thickness Distribution of Quartz Crystal Wafer by Utilizing Atmospheric Pressure Plasma. , 2006, , .		0
114	Polishing Characteristics of Silicon Carbide by Plasma Chemical Vaporization Machining. Japanese Journal of Applied Physics, 2006, 45, 8277-8280.	1.5	26
115	Fabrication of small complex-shaped optics by plasma chemical vaporization machining with a microelectrode. Applied Optics, 2006, 45, 5897.	2.1	12
116	At-wavelength figure metrology of total reflection mirrors in hard x-ray region. , 2006, , .		0
117	Novel abrasive-free planarization of 4H-SiC (0001) using catalyst. Journal of Electronic Materials, 2006, 35, L11-L14.	2.2	114
118	At-wavelength figure metrology of hard x-ray focusing mirrors. Review of Scientific Instruments, 2006, 77, 063712.	1.3	63
119	Ultraprecision Machining Utilizing Numerically Controlled Scanning of Localized Atmospheric Pressure Plasma. Japanese Journal of Applied Physics, 2006, 45, 8270-8276.	1.5	20
120	High-Spatial-Resolution Machining Utilizing Atmospheric Pressure Plasma: Machining Characteristics of Silicon. Japanese Journal of Applied Physics, 2006, 45, 8281-8285.	1.5	1
121	Development of a Mirror Manipulator for Hard X-ray Microscopy with High Resolution. Journal of the Japan Society for Precision Engineering Contributed Papers, 2006, 72, 884-888.	0.0	0
122	Hard x-ray nano-focusing at 40nm level using K-B mirror optics for nanoscopy/spectroscopy. , 2005, , .		4
123	Creation of perfect surfaces. Journal of Crystal Growth, 2005, 275, 39-50.	1.5	52
124	Improvement of thickness uniformity of quartz crystal wafer by numerically controlled plasma CVM. , 2005, 5869, 103.		3
125	Relative angle determinable stitching interferometry for hard x-ray reflective optics. Review of Scientific Instruments, 2005, 76, 045102.	1.3	119
126	Improvement of the thickness distribution of a quartz crystal wafer by numerically controlled plasma chemical vaporization machining. Review of Scientific Instruments, 2005, 76, 096103.	1.3	16

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127	Element Array by Scanning X-ray Fluorescence Microscopy after Cis-Diamminedichloro-Platinum(II) Treatment. Cancer Research, 2005, 65, 4998-5002.	0.9	64
128	Hard X-ray Diffraction-Limited Nanofocusing with Kirkpatrick-Baez Mirrors. Japanese Journal of Applied Physics, 2005, 44, L539-L542.	1.5	95
129	Wave-optical evaluation of interference fringes and wavefront phase in a hard-x-ray beam totally reflected by mirror optics. Applied Optics, 2005, 44, 6927.	2.1	46
130	Fabrication of elliptically figured mirror for focusing hard x rays to size less than 50nm. Review of Scientific Instruments, 2005, 76, 063708.	1.3	63
131	Focusing Hard X-rays to Sub-50 nm Size by Elliptically Figured Mirror. , 2005, , .		0
132	Fabrication of Ultraprecisely Figured Elliptical Mirror for Nano-Focusing of Hard X-ray and Evaluation of Focusing Properties. Journal of the Japan Society for Precision Engineering Contributed Papers, 2005, 71, 1137-1140.	0.0	1
133	Improvement of Thickness Uniformity of Quartz Wafer by Numerically Controlled Plasma CVM. Journal of the Japan Society for Precision Engineering Contributed Papers, 2005, 71, 655-659.	0.0	0
134	Stitching Interferometry for Surface Figure Measurement of X-ray Reflective Optics. , 2005, , .		0
135	Thinning of silicon-on-insulator wafers by numerically controlled plasma chemical vaporization machining. Review of Scientific Instruments, 2004, 75, 942-946.	1.3	40
136	Fabrication technology of hard x-ray aspherical mirror optics and application to nanospectroscopy. , 2004, , .		9
137	Image quality improvement in a hard X-ray projection microscope using total reflection mirror optics. Journal of Synchrotron Radiation, 2004, 11, 343-346.	2.4	28
138	Fabrication technology of ultraprecise mirror optics to realize hard x-ray nanobeam. , 2004, , .		2
139	Wave-optical and ray-tracing analysis to establish a compact two-dimensional focusing unit using K-B mirror arrangement. , 2004, , .		4
140	Microstitching interferometry for nanofocusing mirror optics. , 2004, , .		3
141	Development of a figure correction method having spatial resolution close to 0.1 mm. , 2004, 5193, 105.		4
142	Fabrication of elliptical mirror at nanometer-level accuracy for hard x-ray focusing by numerically controlled plasma chemical vaporization machining. Review of Scientific Instruments, 2003, 74, 4549-4553.	1.3	99
143	Two-dimensional Submicron Focusing of Hard X-rays by Two Elliptical Mirrors Fabricated by Plasma Chemical Vaporization Machining and Elastic Emission Machining. Japanese Journal of Applied Physics, 2003, 42, 7129-7134.	1.5	57
144	Microstitching interferometry for x-ray reflective optics. Review of Scientific Instruments, 2003, 74, 2894-2898.	1.3	149

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145	Fabrication of optics by use of plasma chemical vaporization machining with a pipe electrode. Applied Optics, 2002, 41, 3971.	2.1	32
146	Nearly diffraction-limited line focusing of a hard-X-ray beam with an elliptically figured mirror. Journal of Synchrotron Radiation, 2002, 9, 313-316.	2.4	62
147	Ultraprecision Machining. Ultra-precision Machining by Plasma CVM.. Hyomen Kagaku, 2001, 22, 160-166.	0.0	0
148	Development of plasma chemical vaporization machining. Review of Scientific Instruments, 2000, 71, 4627.	1.3	108
149	The study of fabrication of the x-ray mirror by numerically controlled plasma chemical vaporization machining: Development of the machine for the x-ray mirror fabrication. Review of Scientific Instruments, 2000, 71, 4620.	1.3	60
150	First-principles simulations of removal process in EEM (Elastic Emission Machining). Computational Materials Science, 1999, 14, 232-235.	3.0	48
151	Computer numerically controlled plasma chemical vaporization machining with a pipe electrode for optical fabrication. Applied Optics, 1998, 37, 5198.	2.1	50
152	Plasma Chemical Vaporization Machining (CVM) for Fabrication of Optics. Japanese Journal of Applied Physics, 1998, 37, L894-L896.	1.5	10
153	Temperature Dependence of Plasma Chemical Vaporization Machining of Silicon and Silicon Carbide. Materials Science Forum, 0, 600-603, 847-850.	0.3	17
154	Influence of the UV Light Intensity on the Photoelectrochemical Planarization Technique for Gallium Nitride. Materials Science Forum, 0, 645-648, 795-798.	0.3	8
155	Thinning of SiC Wafer by Plasma Chemical Vaporization Machining. Materials Science Forum, 0, 645-648, 857-860.	0.3	9
156	Thinning of 2-Inch SiC Wafer by Plasma Chemical Vaporization Machining Using Cylindrical Rotary Electrode. Materials Science Forum, 0, 679-680, 481-484.	0.3	7
157	Plasma Chemical Vaporization Machining of Silicon Carbide Wafer Using Flat-Bar Electrode with Multiple Gas Nozzles. Advanced Materials Research, 0, 497, 160-164.	0.3	3
158	Fabrication of Ultrathin Bragg Beam Splitter by Plasma Chemical Vaporization Machining. Key Engineering Materials, 0, 523-524, 40-45.	0.4	8
159	Development of an Ultraprecise Piezoelectric Deformable Mirror for Adaptive X-Ray Optics. Key Engineering Materials, 0, 523-524, 50-53.	0.4	0
160	Cutting of SiC Wafer by Atmospheric-Pressure Plasma Etching with Wire Electrode. Materials Science Forum, 0, 717-720, 865-868.	0.3	5
161	Back-Side Thinning of Silicon Carbide Wafer by Plasma Etching Using Atmospheric-Pressure Plasma. Key Engineering Materials, 0, 516, 108-112.	0.4	3
162	Basic Experiment on Atmospheric-Pressure Plasma Etching with Slit Aperture for High-Efficiency Dicing of SiC Wafer. Materials Science Forum, 0, 740-742, 813-816.	0.3	1

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163	Study of Terminated Species on 4H-SiC (0001) Surfaces Planarized by Catalyst-Referred Etching. Materials Science Forum, 0, 740-742, 510-513.	0.3	2
164	4H-SiC Planarization Using Catalyst-Referred Etching with Pure Water. Materials Science Forum, 0, 778-780, 722-725.	0.3	5
165	Thinning of a Two-Inch Silicon Carbide Wafer by Plasma Chemical Vaporization Machining Using a Slit Electrode. Materials Science Forum, 0, 778-780, 750-753.	0.3	4
166	Investigation of the Barrier Heights for Dissociative Adsorption of HF on SiC Surfaces in the Catalyst-Referred Etching Process. Materials Science Forum, 0, 778-780, 726-729.	0.3	1
167	Basic Study on Etching Selectivity of Plasma Chemical Vaporization Machining by Introducing Crystallographic Damage into Work Surface. Key Engineering Materials, 0, 625, 550-553.	0.4	5
168	Planarization of 6-Inch 4H-SiC Wafer Using Catalyst-Referred Etching. Materials Science Forum, 0, 821-823, 537-540.	0.3	1
169	Improvement of I-V Characteristics of Schottky Barrier Diode by 4H-SiC Surface Planarization. Materials Science Forum, 0, 821-823, 567-570.	0.3	3
170	Cause of Etch Pits during the High Speed Plasma Etching of Silicon Carbide and an Approach to Reduce their Size. Materials Science Forum, 0, 1004, 161-166.	0.3	4